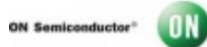
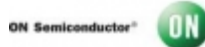
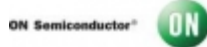
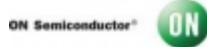


specificazioni	
Modello di prodotti	FQA32N20C
fabbricante	Fairchild/ON Semiconductor
Descrizione	MOSFET N-CH 200V 32A TO-3P
Categoria	Prodotti a semiconduttore discreti > Transistor-FET,
Stato parte	6138 pcs Stock
Vgs (th) (max) a Id	4V @ 250μA
Tecnologia	MOSFET (Metal Oxide)
Contenitore dispositivo fornitore	TO-3PN
Serie	QFET®
Rds On (max) a Id, Vgs	82 mOhm @ 16A, 10V
Dissipazione di potenza (max)	204W (Tc)
imballaggio	Tube
Contenitore / involucri	TO-3P-3, SC-65-3
temperatura di esercizio	-55°C ~ 150°C (TJ)
Tipo montaggio	Through Hole
Capacità di ingresso (Ciss) (Max) @ Vds	2220pF @ 25V
Carica Gate (Qg) (Max) @ Vgs	110nC @ 10V
Tipo FET	N-Channel
Caratteristica FET	-
Tensione drain-source (Vdss)	200V
Corrente - Drain continuo (Id) @ 25 ° C	32A (Tc)

 FQA28N50_F109 Fairchild/ON Semiconductor MOSFET N-CH 500V 28.4A TO-3PN	 FQA30N40 MOS FAIRCHILD FAIRCHILD TO-3P	 FQA32N20C AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 32A TO-3P	 FQA33N10L AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 36A TO-3P
 FQA30N40 Fairchild/ON Semiconductor MOSFET N-CH 400V 30A TO-3P	 FQA33N10 AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 36A TO-3P	 FQA28N50_F109 AMI Semiconductor / ON Semiconductor MOSFET N-CH 500V 28.4A TO-3PN	 FQA33N10L Fairchild/ON Semiconductor MOSFET N-CH 100V 36A TO-3P

Di Più

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